



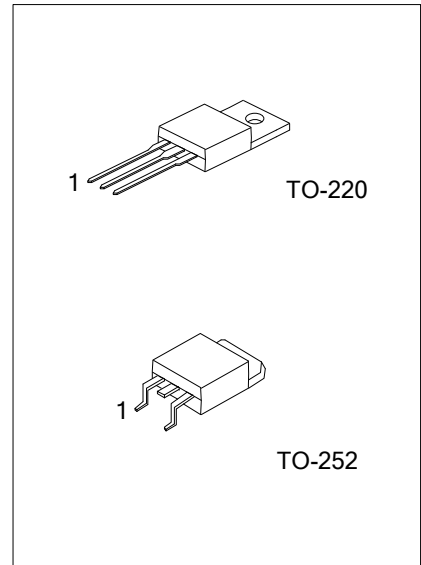
MJE2955T

PNP SILICON TRANSISTOR

HIGH VOLTAGE TRANSISTOR

DESCRIPTION

The UTC **MJE2955T** is designed for general purpose of amplifier and switching applications.



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
MJE2955TL-TA3-T	MJE2955TG-TA3-T	TO-220	B	C	E	Tube
MJE2955TL-TN3-R	MJE2955TG-TN3-R	TO-252	B	C	E	Tape Reel

Note: B: Base C: Collector E: Emitter

<p>MJE2955TL-TA3-R</p> <p>(1)Packing Type (2)Package Type (3)Lead Plating</p>	<p>(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TN3: TO-252 (3) L: Lead Free Plating, G: Halogen Free</p>
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■ ABSOLUTE MAXIMUM RATING

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	-70	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector current	I_C	-10	A
Base Current	I_B	-6	A
Power Dissipation ($T_A=25^\circ\text{C}$)	TO-220	75	W
	TO-252	20	
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

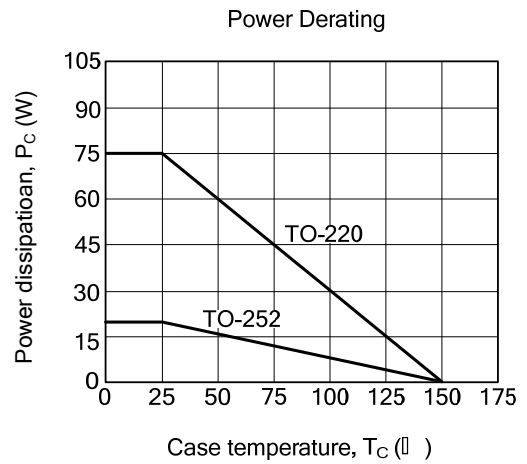
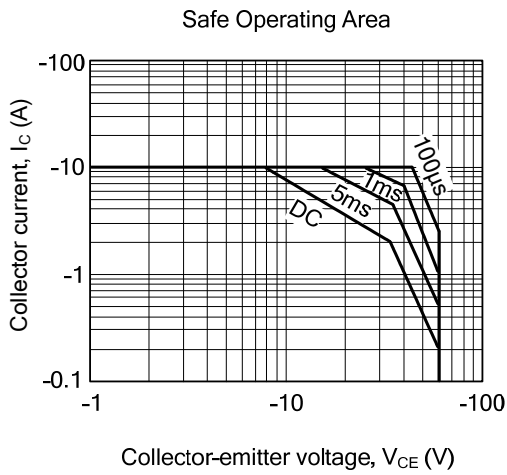
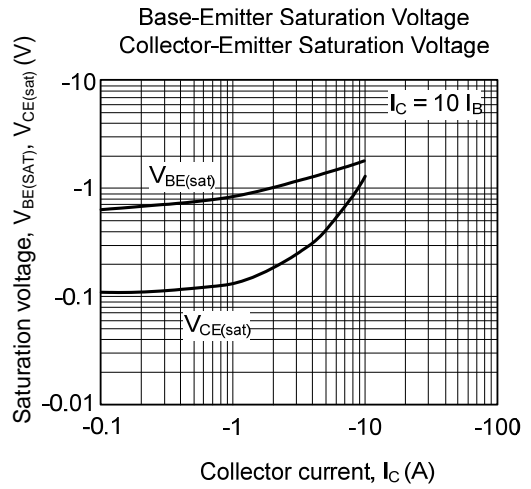
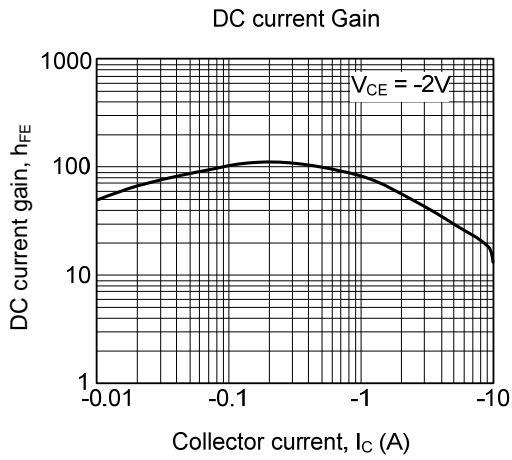
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. The device is guaranteed to meet performance specification within $0^\circ\text{C} \sim 70^\circ\text{C}$

■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-200\text{mA}$	-60			V
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-10\text{mA}$	-70			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-10\text{mA}$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-70\text{V}$			-1	mA
	I_{CEO}	$V_{CE}=-30\text{V}$			-700	μA
	I_{CEX}	$V_{CE}=-70\text{V}, V_{EB(OFF)}=-1.5\text{V}$			-1	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5\text{V}$			-5	mA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)1}$	$I_C=-4\text{A}, I_B=-0.4\text{A}$			-1.1	V
	$V_{CE(SAT)2}$	$I_C=-10\text{A}, I_B=-3.3\text{A}$			-8.0	
Base-Emitter on Voltage	$V_{BE(ON)}$	$V_{CE}=-4\text{V}, I_C=-4\text{A}$			-1.8	V
DC Current Gain	h_{FE1}	$I_C=-4\text{A}, V_{CE}=-4\text{V}$	20		100	
	h_{FE2}	$I_C=-10\text{A}, V_{CE}=-4\text{V}$	5			
Current Gain Bandwidth Product	f_T	$V_{CE}=-10\text{V}, I_C=-0.5\text{A}, f=1\text{MHz}$	2			MHZ

TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.